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March 28, 2003

CUSTOMER NO.: 31561

Attorney Docket No.: 7554-US-PA

Page(s): Cover +7

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FAX NO.: 002-1-703-872-9318

TO: UNITED STATES PATENT AND TRADEMARK OFFICE  
Mrs. YOHA, CONNIE C.

MAR 28 2003

TECHNOLOGY CENTER 2800

MESSAGE: Enclosed please the Amendment in Response to the Office Action dated  
January 30, 2003 for the Application No.: 10/064,266.

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Customer No.: 31561  
Application No.: 10/064,266

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

4/1/03

In re application of: ) I hereby certify that this correspondence and all  
Application No.: 10/064,266 ) marked attachments are being deposited with the  
Filed: June 27, 2002 ) United States Postal Service as first class mail in  
For: METHOD FOR FABRICATING FLASH ) an envelope addressed to: Assistant  
MEMORY ) Commissioner for Patents, Washington, D.C.  
20231, on )  
Applicant: Chang et al. )  
Examiner: Chaudhari, Chandra P. )  
Art Unit 2813 )

Smith

No fee is believed to be due in connection with this amendment and response to Office Action.

AMENDMENT AND RESPONSE TO OFFICE ACTION

FAX RECEIVED

Commissioner for Patents  
Washington, DC 20231

MAR 28 2003

TECHNOLOGY CENTER 2800

Sir:

The Office Action mailed on January 30, 2003 (Paper No. 2) has been carefully considered. In response thereto, please enter the following amendments and consider the following remarks.

REMARKS

1. (once amended) A method for fabricating a flash memory, comprising the steps of:
- forming a stacked gate structure and a source/drain on a substrate;
- forming an inter-layer dielectrics on the substrate; and

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